

2SD1137

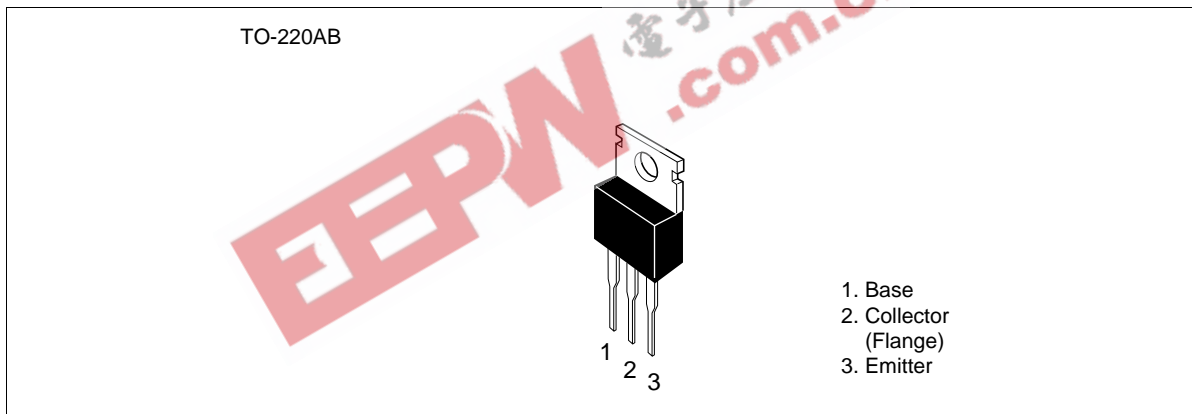
Silicon NPN Triple Diffused

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Application

Low frequency power amplifier TV vertical deflection output complementary pair with 2SB860

Outline



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	100	V
Emitter to base voltage	V_{EBO}	4	V
Collector current	I_{C}	4	A
Collector peak current	$I_{\text{C (peak)}}$	5	A
Collector power dissipation	P_{C}	1.8	W
	P_{C}^{*1}	40	W
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-45 to +150	$^\circ\text{C}$

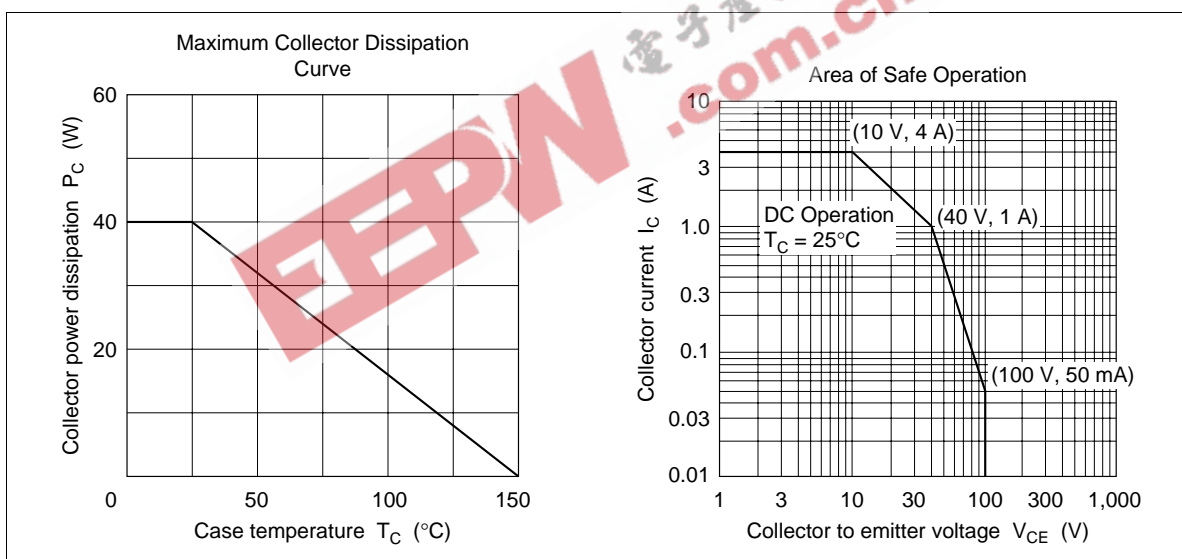
Note: 1. Value at $T_{\text{c}} = 25^\circ\text{C}$.

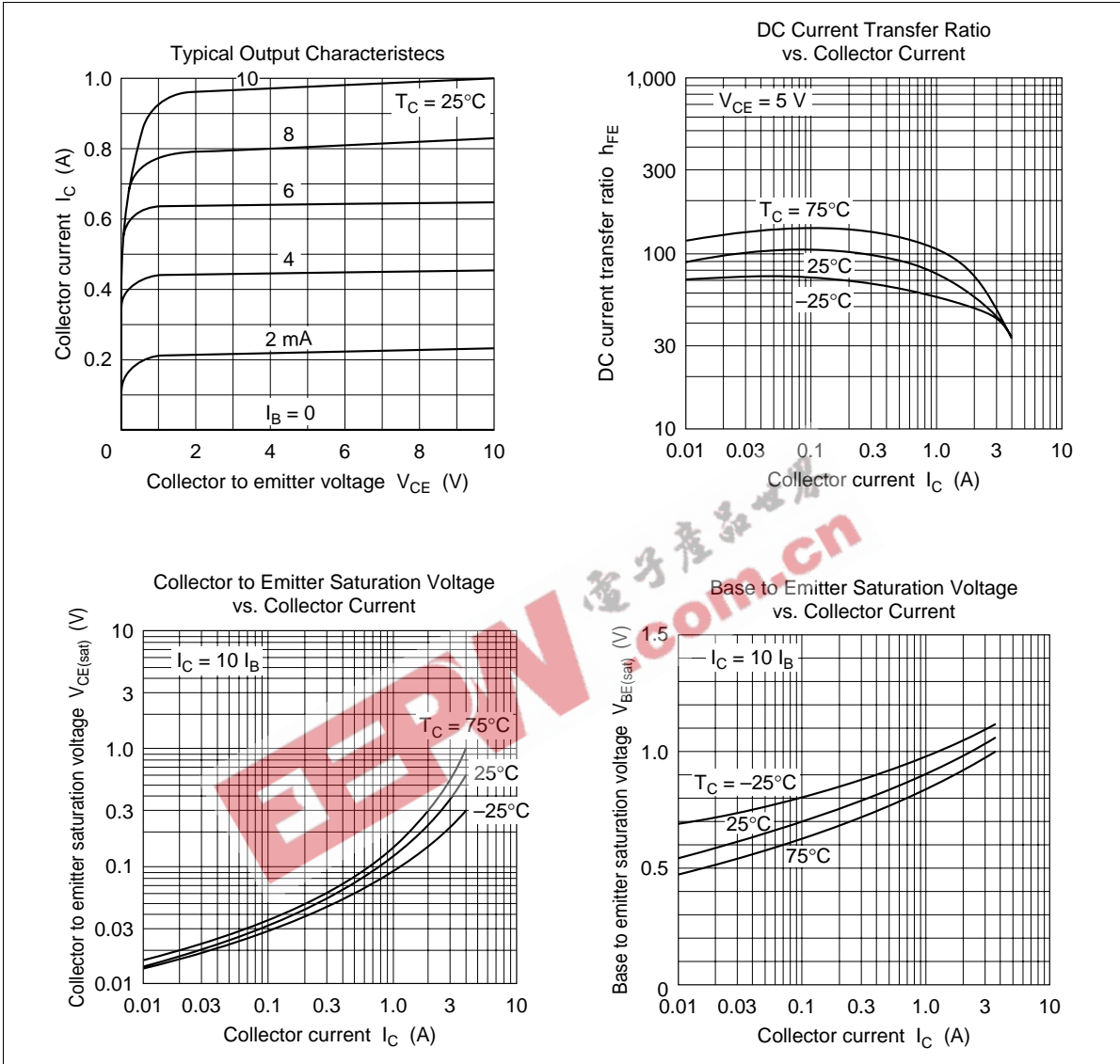
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Electrical Characteristics (T_a = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	100	—	—	V	$I_C = 10 \text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	—	—	V	$I_E = 1 \text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CEO}	—	—	100	μA	$V_{CE} = 80 \text{ V}$, $R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	50	μA	$V_{EB} = 3.5 \text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}	50	—	250		$V_{CE} = 4 \text{ V}$
		25	—	350		$I_C = 0.5 \text{ A}^{*1}$ $I_C = 50 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C = 1 \text{ A}$, $I_B = 0.1 \text{ A}$

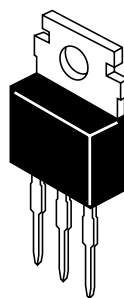
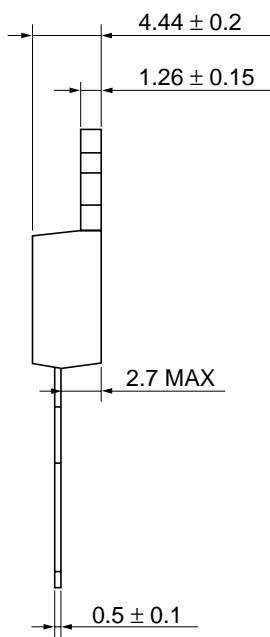
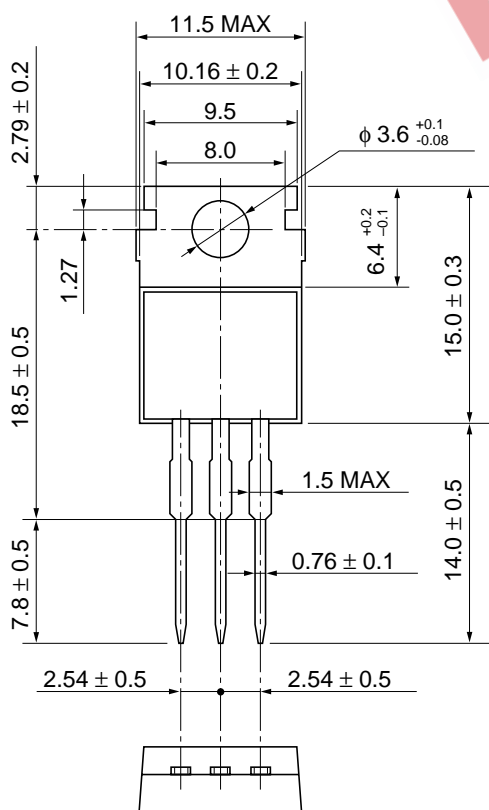
Note: 1. Pulse test.





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Unit: mm



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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